

#4 *per Ammt. A*
4-22-02
estates

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Eiji Nishibe et al.

Art Unit : Unknown

Serial No. : to be determined

Examiner : Unknown

Filed : August 31, 2001

Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Prior to examination, please amend the application as follows:

In the abstract:

Insert the abstract after the last line on page 33.

~A semiconductor device is provided with a gate electrode formed over a substrate that has gate oxide films disposed thereon. Source-drain regions of low and high concentration are formed next to the gate electrode. A diffusion region width of the source side of the source-drain regions is smaller than at least a diffusion region width of the drain side.~

CERTIFICATE OF MAILING BY EXPRESS MAIL

Express Mail Label No. EF353814359US

I hereby certify under 37 CFR §1.10 that this correspondence is being deposited with the United States Postal Service as Express Mail Post Office to Addressee with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

August 31, 2001

Date of Deposit

Francisco Robles

Signature

Francisco Robles

Typed or Printed Name of Person Signing Certificate